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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/734,749	10/734,749 12/11/2003		Haoren Zhuang	14580-045001 / FP2078	9525	
20985	7590	02/08/2006	EXAMINER		NER	
FISH & RICHARDSON, PC				CHACKO DAV	CHACKO DAVIS, DABORAH	
P.O. BOX 1022 MINNEAPOLIS, MN 55440-1022				ART UNIT	PAPER NUMBER	
	,			1756		

DATE MAILED: 02/08/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

•			(-)				
		Application No.	Applicant(s)				
		10/734,749	ZHUANG, HAOREN				
	Office Action Summary	Examiner	Art Unit				
		Daborah Chacko-Davis	1756				
Period f	The MAILING DATE of this communication apports or Reply	pears on the cover sheet with the c	orrespondence address				
WHI - Extended aftended - If No - Fail Any	HORTENED STATUTORY PERIOD FOR REPL CHEVER IS LONGER, FROM THE MAILING D ensions of time may be available under the provisions of 37 CFR 1.1 or SIX (6) MONTHS from the mailing date of this communication. O period for reply is specified above, the maximum statutory period vure to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tin will apply and will expire SIX (6) MONTHS from , cause the application to become ABANDONE	N. nely filed the mailing date of this communication. ED (35 U.S.C. § 133).				
Status							
1)⊠	Responsive to communication(s) filed on 29 N	l <u>ovember 2005</u> .					
· ·		action is non-final.					
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposi	tion of Claims						
5)□	4) ⊠ Claim(s) 1-7 and 12-17 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. 5) □ Claim(s) is/are allowed.						
6)⊠							
7)∐ 8)□	Claim(s) is/are objected to. Claim(s) are subject to restriction and/o	r election requirement					
0,	oralings are subject to restriction and/o	r ciconomicquirement.					
Applicat	tion Papers						
9)□	The specification is objected to by the Examine	er.					
10)	10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.						
	Applicant may not request that any objection to the	• • • • • • • • • • • • • • • • • • • •	` '				
11) <u>□</u>	Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Ex						
Priority	under 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 							
Attachme i 1)	nt(s) ce of References Cited (PTO-892)	4) 🔲 Interview Summary	(PTO-413)				
2) 🔲 Noti 3) 🔯 Info	ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) er No(s)/Mail Date 12/05.	Paper No(s)/Mail Da					

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-7, 12-17, are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patent Application Publication No. 2003/0119273 (Aggarwal et al) in view of U.S. Patent Application Publication No. 2004/0164293 (Maloney et al).

Aggarwal, in [0065], [0066], [0067], [0068], [0069], [0070], [0090], [0094], discloses applying a hard mask layer on the capacitor device, applying a photoresist pattern (photolithography performed) to the hard mask to form a patterned layer, and performing a heat treatment in an O₂/N₂ atmosphere to convert the hard mask material to corresponding oxides (TiO₂, TiAlO) and nitrides (TiAlN, TiN). Aggarwal, in [0076], discloses an etch process that etches through the photoresist pattern to form the hard mask pattern, wherein the hard mask pattern is used for subsequent etch processes (claims 1, 2, 7, 12-13). Aggarwal, in [0051], discloses a sol-gel process for depositing the hard mask material (claim 14). Aggarwal, in [0014], discloses that the device is a FeRAM device (claims 15-17).

The difference between the claims and Aggarwal is that Aggarwal does not disclose that the hard mask layer is a photosensitive sol-gel layer. Aggarwal does not

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disclose that the sol gel layer is a titanium organic gel layer (claim 3). Aggarwal does not disclose that the sol gel layer is a titanium-aluminum organic gel layer (claim 4). Aggarwal does not disclose that the sol-gel layer is a mixture of titanium alkoxides with ethyl acetoactate (claim 5). Aggarwal does not disclose that the sol-gel layer is a mixture of one or more (TiOEt)₄ or Ti(OEt)₄ (claim 6).

Maloney, in [0144], [0145], [0146], [0147], discloses that the hard mask layer is a photosensitive sol-gel layer comprising a metal complex precursor of the claimed composition.

Therefore, it would be obvious to a skilled artisan to modify Aggarwal by employing the photosensitive sol-gel composition suggested by Maloney because Maloney, in [0173], discloses that employing the photosensitive (metal precursor) solgel layer as the hard mask layer enables low temperature processing and a four-fold reduction in carbon residues.

Response to Arguments

- 3. Applicant's arguments filed November 29, 2005, have been fully considered but they are not persuasive. The 103 rejection made in the previous office action (paper no. 0624) is maintained.
- A) Applicants argue that Aggarwal et al., does not disclose a photosensitive sol-gel layer hard mask.

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Aggarwal et al., is not depended upon to disclose a photosensitive sol-gel layer used as a hard mask, Maloney et al., depended upon to disclose the use of a photosensitive sol-gel layer that is converted to a hard mask layer.

B) Applicants argue that Aggarwal et al., does not disclose that the claimed sol-gel layer is converted to a hardmask by thermal decomposition treatment.

Aggarwal teaches the use of a hard mask layer that is patterned and then heattreated in a nitrogen atmosphere to form a corresponding nitride inorder to perform as a hard mask pattern.

C) Applicants argue that Maloney et al., does not disclose applying a thermal decomposition treatment to convert the sol-gel layer to a metal nitride.

Maloney et al., is not depended upon to disclose the conversion of the sol-gel layer to a nitride. However, Maloney teaches the use of sol-gel precursors that can be converted to hard mask material. Aggarwal is depended upon to disclose the formation of the metal nitride by nitridation of the patterned hard mask material.

Conclusion

4. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any

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extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Daborah Chacko-Davis whose telephone number is (571) 272-1380. The examiner can normally be reached on M-F 9:30 - 6:00. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mark F Huff can be reached on (571) 272-1385. The fax phone number for the organization where this application or proceeding is assigned is (571) 273-8300. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

dcd

February 2, 2006.

JOHN A. MCPHERSON PRIMARY EXAMINER